Code No: 09A70412

R09

JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD B. Tech IV Year I Semester Examinations, May/June - 2013 VLSI Design

(Common to ECE, EIE, BME, IT, ETM, ECM, ICE)

Time: 3 Hours

Max. Marks: 75

Answer any Five Questions All Questions Carry Equal Marks

1.a) b)	Explain the fabrication process of p-well CMOS Explain about ion implantation mechanism for			diagrams. [9+6	5]
2.a)	Find the drain-to-source current versus voltage relationship of I _{ds} vs Vds of nMOS transistor.				
b)	Explain about latch-up effect in CMOS transisto	or.		[9+6]
3.a) b)	Draw the stick diagram of CMOS two input NAND gate. Explain about various contact cuts are used for CMOS transistor design and				
	fabrication.			[7+8]
4.a) b)	Implement two input EX-NOR gate by using transmission gates. Explain about pseudo-nMOS logic with an example? Compare the performance of the compare the compare the compare the performance of the compare the compare the compare the compare the compare the performance of the compare the c				0
	pseudo nMOS logic with nMOS logic?	34.	13 Exp.	[7+8	
5.a) b)	Explain the operation of 4X4 Barrel Shifter with Design a 4 bit Comparator which gives outputs			. [8+7	1
6.a)	Explain the operation of DRAM Cell.			55	,
b)	Explain about Serial access memories.			[8+7]
7.a)	Implement the following functions by using PL: $F1(a,b,c) = \sum m(1,2,4,7)$	A			
b)	F2(a,b,c)= \sum m(1,2,3,7) Draw and explain the architecture of FPGA?			[7+8]
8.a)	Explain the stuck at fault models with suitable e				
b)	Explain how an improved layout can be reduced	i taults ii	n CMOS circ	ouits. [8+7	